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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	150
Number of Gates	36000
Voltage - Supply	3V ~ 3.6V, 4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	176-LQFP
Supplier Device Package	176-TQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a42mx24-ftqg176

Email: info@E-XFL.COM

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Figure 5 • A42MX24 and A42MX36 D-Module Implementation



Figure 6 • A42MX36 Dual-Port SRAM Block



3.2.3 Routing Structure

The MX architecture uses vertical and horizontal routing tracks to interconnect the various logic and I/O modules. These routing tracks are metal interconnects that may be continuous or split into segments. Varying segment lengths allow the interconnect of over 90% of design tracks to occur with only two antifuse connections. Segments can be joined together at the ends using antifuses to increase their lengths up to the full length of the track. All interconnects can be accomplished with a maximum of four antifuses.

3.2.3.1 Horizontal Routing

Horizontal routing tracks span the whole row length or are divided into multiple segments and are located in between the rows of modules. Any segment that spans more than one-third of the row length is considered a long horizontal segment. A typical channel is shown in Figure 7, page 10. Within horizontal routing, dedicated routing tracks are used for global clock networks and for power and ground tie-off tracks. Non-dedicated tracks are used for signal nets.

3.2.3.2 Vertical Routing

Another set of routing tracks run vertically through the module. There are three types of vertical tracks: input, output, and long. Long tracks span the column length of the module, and can be divided into multiple segments. Each segment in an input track is dedicated to the input of a particular module; each segment in an output track is dedicated to the output of a particular module. Long segments are uncommitted and can be assigned during routing.

Each output segment spans four channels (two above and two below), except near the top and bottom of the array, where edge effects occur. Long vertical tracks contain either one or two segments. An example of vertical routing tracks and segments is shown in Figure 7, page 10.

3.3.7 Low Power Mode

42MX devices have been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when exiting Low Power Mode. I/Os can be driven during LP mode, and clock pins should be driven HIGH or LOW and should not float to avoid drawing current. To exit LP mode, the LP pin must be pulled LOW for over 200 µs to allow for charge pumps to power up, and device initialization will begin.

3.4 **Power Dissipation**

The general power consumption of MX devices is made up of static and dynamic power and can be expressed with the following equation.

3.4.1 General Power Equation

P = [ICCstandby + ICCactive]*VCCI + IOL*VOL*N + IOH*(VCCI - VOH)*M

EQ 1

where:

- ICCstandby is the current flowing when no inputs or outputs are changing.
- ICCactive is the current flowing due to CMOS switching.
- IOL, IOH are TTL sink/source currents.
- VOL, VOH are TTL level output voltages.
- N equals the number of outputs driving TTL loads to VOL.
- M equals the number of outputs driving TTL loads to VOH.

Accurate values for N and M are difficult to determine because they depend on the family type, on design details, and on the system I/O. The power can be divided into two components: static and active.

3.4.2 Static Power Component

The static power due to standby current is typically a small component of the overall power consumption. Standby power is calculated for commercial, worst-case conditions. The static power dissipation by TTL loads depends on the number of outputs driving, and on the DC load current. For instance, a 32-bit bus sinking 4mA at 0.33V will generate 42mW with all outputs driving LOW, and 140mW with all outputs driving HIGH. The actual dissipation will average somewhere in between, as I/Os switch states with time.

3.4.3 Active Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. Dynamic power consumption is frequency-dependent and is a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitances due to PC board traces and load device inputs. An additional component of the active power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

The power dissipated by a CMOS circuit can be expressed by the equation:

$$Power(\mu W) = C_{EO}^* VCCA2^* F(1)$$

where:

C_{EQ} = Equivalent capacitance expressed in picofarads (pF)

EQ 2

Additionally, the back-annotation flow is compatible with all the major simulators and the simulation results can be cross-probed with Silicon Explorer II, Microsemi's integrated verification and logic analysis tool. Another tool included in the Libero software is the SmartGen macro builder, which easily creates popular and commonly used logic functions for implementation into your schematic or HDL design.

Microsemi's Libero software is compatible with the most popular FPGA design entry and verification tools from companies such as Mentor Graphics, Synopsys, and Cadence design systems.

See the Libero IDE web content at www.microsemi.com/soc/products/software/libero/default.aspx for further information on licensing and current operating system support.

3.6 Related Documents

The following sections give the list of related documents which can be refered for this datasheet.

3.6.1 Application Notes

- AC278: BSDL Files Format Description
- AC225: Programming Antifuse Devices
- AC168: Implementation of Security in Microsemi Antifuse FPGAs

3.6.2 User Guides and Manuals

- Antifuse Macro Library Guide
- Silicon Sculptor Programmers User Guide

3.6.3 Miscellaneous

Libero IDE Flow Diagram

3.7 5.0 V Operating Conditions

The following tables show 5.0 V operating conditions.

Table 12 • Absolute Maximum Ratings for 40MX Devices*

Symbol	Parameter	Limits	Units
VCC	DC Supply Voltage	-0.5 to +7.0	V
VI	Input Voltage	-0.5 to VCC+0.5	V
VO	Output Voltage	-0.5 to VCC+0.5	V
t _{STG}	Storage Temperature	-65 to +150	°C

Note: *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the recommended operating conditions.

Table 13 • Absolute Maximum Ratings for 42MX Devices*

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	-0.5 to +7.0	V
VCCA	DC Supply Voltage for Array	-0.5 to +7.0	V
VI	Input Voltage	-0.5 to VCCI+0.5	V
VO	Output Voltage	-0.5 to VCCI+0.5	V
t _{STG}	Storage Temperature	-65 to +150	°C



Figure 16 • Typical Output Drive Characteristics (Based Upon Measured Data)

3.9.4 Junction Temperature (T_J)

The temperature variable in the Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because the heat generated from dynamic power consumption is usually hotter than the ambient temperature. The following equation can be used to calculate junction temperature.

Junction Temperature = $\Delta T + T_a(1)$

EQ 4

where:

- T_a = Ambient Temperature
- ΔT = Temperature gradient between junction (silicon) and ambient
- $\Delta T = \theta_{ia} * P(2)$
- P = Power
- θ_{ia} = Junction to ambient of package. θ_{ia} numbers are located in Table 27, page 29.

3.9.5 Package Thermal Characteristics

The device junction-to-case thermal characteristic is θ_{jc} , and the junction-to-ambient air characteristic is θ_{ja} . The thermal characteristics for θ_{ja} are shown with two different air flow rates.

The maximum junction temperature is 150°C.

Maximum power dissipation for commercial- and industrial-grade devices is a function of θ_{ia} .

A sample calculation of the absolute maximum power dissipation allowed for a TQ176 package at commercial temperature and still air is given in the following equation

MaximumPowerAllowed =
$$\frac{\text{Max} \cdot \text{junction temp} \cdot (^{\circ}\text{C}) - \text{Max} \cdot \text{ambient temp} \cdot (^{\circ}\text{C})}{\theta_{ja}(^{\circ}(\text{C/W}))} = \frac{150^{\circ}\text{C} - 70^{\circ}\text{C}}{(28^{\circ}\text{C})/\text{W}} = 2.86\text{W}$$

The maximum power dissipation for military-grade devices is a function of θ_{jc} . A sample calculation of the absolute maximum power dissipation allowed for CQFP 208-pin package at military temperature and still air is given in the following equation

MaximumPowerAllowed =
$$\frac{\text{Max} \cdot \text{junction temp} \cdot (^{\circ}\text{C}) - \text{Max} \cdot \text{ambient temp} \cdot (^{\circ}\text{C})}{\theta_{jc}(^{\circ}(\text{C}/\text{W}))} = \frac{150^{\circ}\text{C} - 125^{\circ}\text{C}}{(6.3^{\circ}\text{C})/\text{W}} = 3.97\text{W}$$

EQ 6

EQ 5

Table 27 • Package Thermal Characteristics

			θ_{ja}			
Plastic Packages	Pin Count	θ_{jc}	Still Air	1.0 m/s 200 ft/min.	2.5 m/s 500 ft/min.	Units
Plastic Quad Flat Pack	100	12.0	27.8	23.4	21.2	°C/W
Plastic Quad Flat Pack	144	10.0	26.2	22.8	21.1	°C/W
Plastic Quad Flat Pack	160	10.0	26.2	22.8	21.1	°C/W
Plastic Quad Flat Pack	208	8.0	26.1	22.5	20.8	°C/W
Plastic Quad Flat Pack	240	8.5	25.6	22.3	20.8	°C/W
Plastic Leaded Chip Carrier	44	16.0	20.0	24.5	22.0	°C/W
Plastic Leaded Chip Carrier	68	13.0	25.0	21.0	19.4	°C/W
Plastic Leaded Chip Carrier	84	12.0	22.5	18.9	17.6	°C/W
Thin Plastic Quad Flat Pack	176	11.0	24.7	19.9	18.0	°C/W
Very Thin Plastic Quad Flat Pack	80	12.0	38.2	31.9	29.4	°C/W
Very Thin Plastic Quad Flat Pack	100	10.0	35.3	29.4	27.1	°C/W
Plastic Ball Grid Array	272	3.0	18.3	14.9	13.9	°C/W
Ceramic Packages						
Ceramic Pin Grid Array	132	4.8	25.0	20.6	18.7	°C/W
Ceramic Quad Flat Pack	208	2.0	22.0	19.8	18.0	°C/W
Ceramic Quad Flat Pack	256	2.0	20.0	16.5	15.0	°C/W



Figure 33 • 42MX SRAM Asynchronous Read Operation—Type 2 (Write Address Controlled)

3.10.7 Predictable Performance: Tight Delay Distributions

Propagation delay between logic modules depends on the resistive and capacitive loading of the routing tracks, the interconnect elements, and the module inputs being driven. Propagation delay increases as the length of routing tracks, the number of interconnect elements, or the number of inputs increases.

From a design perspective, the propagation delay can be statistically correlated or modeled by the fanout (number of loads) driven by a module. Higher fanout usually requires some paths to have longer routing tracks.

The MX FPGAs deliver a tight fanout delay distribution, which is achieved in two ways: by decreasing the delay of the interconnect elements and by decreasing the number of interconnect elements per path.

Microsemi's patented antifuse offers a very low resistive/capacitive interconnect. The antifuses, fabricated in 0.45 μ m lithography, offer nominal levels of 100 Ω resistance and 7.0 fF capacitance per antifuse.

MX fanout distribution is also tight due to the low number of antifuses required for each interconnect path. The proprietary architecture limits the number of antifuses per path to a maximum of four, with 90 percent of interconnects using only two antifuses.

3.11 Timing Characteristics

Device timing characteristics fall into three categories: family-dependent, device-dependent, and designdependent. The input and output buffer characteristics are common to all MX devices. Internal routing delays are device-dependent; actual delays are not determined until after place-and-route of the user's design is complete. Delay values may then be determined by using the Designer software utility or by performing simulation with post-layout delays.

3.11.1 Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing critical paths. Critical nets are determined by net property assignment in Microsemi's Designer software prior to placement and routing. Up to 6% of the nets in a design may be designated as critical.

3.11.2 Long Tracks

Some nets in the design use long tracks, which are special routing resources that span multiple rows, columns, or modules. Long tracks employ three and sometimes four antifuse connections, which increase capacitance and resistance, resulting in longer net delays for macros connected to long tracks. Typically, up to 6 percent of nets in a fully utilized device require long tracks. Long tracks add

Table 34 •A40MX02 Timing Characteristics (Nominal 5.0 V Operation) (continued)
(Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C)

			–3 Sp	beed	–2 Sp	beed	–1 Sp	eed	Std S	peed	–F Sp	eed	
Parame	eter / Description	-	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
Input N	Iodule Propagation	Delays											
t _{INYH}	Pad-to-Y HIGH			0.7		0.8		0.9		1.1		1.5	ns
t _{INYL}	Pad-to-Y LOW			0.6		0.7		0.8		1.0		1.3	ns
Input M	Iodule Predicted Ro	outing Delay	ys ¹										
t _{IRD1}	FO = 1 Routing De	lay		2.1		2.4		2.2		3.2		4.5	ns
t _{IRD2}	FO = 2 Routing De	lay		2.6		3.0		3.4		4.0		5.6	ns
t _{IRD3}	FO = 3 Routing De	lay		3.1		3.6		4.1		4.8		6.7	ns
t _{IRD4}	FO = 4 Routing De	lay		3.6		4.2		4.8		5.6		7.8	ns
t _{IRD8}	FO = 8 Routing De	lay		5.7		6.6		7.5		8.8		12.4	ns
Global	Clock Network												
t _{CKH}	Input Low to HIGH	FO = 16 FO = 128		4.6 4.6		5.3 5.3		6.0 6.0		7.0 7.0		9.8 9.8	ns
t _{CKL}	Input High to LOW	FO = 16 FO = 128		4.8 4.8		5.6 5.6		6.3 6.3		7.4 7.4		10.4 10.4	ns
t _{PWH}	Minimum Pulse Width HIGH	FO = 16 FO = 128	2.2 2.4		2.6 2.7		2.9 3.1		3.4 3.6		4.8 5.1		ns
t _{PWL}	Minimum Pulse Width LOW	FO = 16 FO = 128	2.2 2.4		2.6 2.7		2.9 3.01		3.4 3.6		4.8 5.1		ns
t _{CKSW}	Maximum Skew	FO = 16 FO = 128		0.4 0.5		0.5 0.6		0.5 0.7		0.6 0.8		0.8 1.2	ns
t _P	Minimum Period	FO = 16 FO = 128	4.7 4.8		5.4 5.6		6.1 6.3		7.2 7.5		10.0 10.4		ns
f _{MAX}	Maximum Frequency	FO = 16 FO = 128		188 181		175 168		160 154		139 134		83 80	MHz

		–3 Sp	beed	–2 Sp	eed	–1 Sp	eed	Std S	peed	–F Sp	eed	
Parame	eter / Description	Min.	Max.	Units								
TTL Ou	tput Module Timing ⁴											
t _{DLH}	Data-to-Pad HIGH		3.3		3.8		4.3		5.1		7.2	ns
t _{DHL}	Data-to-Pad LOW		4.0		4.6		5.2		6.1		8.6	ns
t _{ENZH}	Enable Pad Z to HIGH		3.7		4.3		4.9		5.8		8.0	ns
t _{ENZL}	Enable Pad Z to LOW		4.7		5.4		6.1		7.2		10.1	ns
t _{ENHZ}	Enable Pad HIGH to Z		7.9		9.1		10.4		12.2		17.1	ns
t _{ENLZ}	Enable Pad LOW to Z		5.9		6.8		7.7		9.0		12.6	ns
d _{TLH}	Delta LOW to HIGH		0.02		0.02		0.03		0.03		0.04	ns/pF
d _{THL}	Delta HIGH to LOW		0.03		0.03		0.03		0.04		0.06	ns/pF
CMOS	Output Module Timing ⁴											
t _{DLH}	Data-to-Pad HIGH		3.9		4.5		5.1		6.05		8.5	ns
t _{DHL}	Data-to-Pad LOW		3.4		3.9		4.4		5.2		7.3	ns
t _{ENZH}	Enable Pad Z to HIGH		3.4		3.9		4.4		5.2		7.3	ns
t _{ENZL}	Enable Pad Z to LOW		4.9		5.6		6.4		7.5		10.5	ns
t _{ENHZ}	Enable Pad HIGH to Z		7.9		9.1		10.4		12.2		17.0	ns
t _{ENLZ}	Enable Pad LOW to Z		5.9		6.8		7.7		9.0		12.6	ns
d _{TLH}	Delta LOW to HIGH		0.03		0.04		0.04		0.05		0.07	ns/pF
d _{THL}	Delta HIGH to LOW		0.02		0.02		0.03		0.03		0.04	ns/pF

Table 34 •A40MX02 Timing Characteristics (Nominal 5.0 V Operation) (continued)
(Worst-Case Commercial Conditions, VCC = 4.75 V, $T_J = 70^{\circ}$ C)

1. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual performance

2. Set-up times assume fanout of 3. Further testing information can be obtained from the Timer utility

3. The hold time for the DFME1A macro may be greater than 0 ns. Use the Timer tool from the Designer software to check

the hold time for this macro.

4. Delays based on 35pF loading

Table 35 •A40MX02 Timing Characteristics (Nominal 3.3 V Operation)
(Worst-Case Commercial Conditions, VCC = 3.0 V, T_J = 70°C)

		-3 Speed		–2 Sp	beed	–1 Sp	beed	Std Speed		-F Speed		
Paramet	er / Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
Logic Mo	odule Propagation Delays											
t _{PD1}	Single Module		1.7		2.0		2.3		2.7		3.7	ns
t _{PD2}	Dual-Module Macros		3.7		4.3		4.9		5.7		8.0	ns
t _{CO}	Sequential Clock-to-Q		1.7		2.0		2.3		2.7		3.7	ns
t _{GO}	Latch G-to-Q		1.7		2.0		2.3		2.7		3.7	ns
t _{RS}	Flip-Flop (Latch) Reset-to-Q		1.7		2.0		2.3		2.7		3.7	ns
Logic Mo	odule Predicted Routing Delays	¹										

		–3 Sp	beed	–2 S	peed	–1 Sp	eed	Std S	Speed	–F S	peed	
Parame	eter / Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
TTL Ou	tput Module Timing ⁵											
t _{DLH}	Data-to-Pad HIGH		2.5		2.7		3.1		3.6		5.1	ns
t _{DHL}	Data-to-Pad LOW		2.9		3.2		3.6		4.3		6.0	ns
t _{ENZH}	Enable Pad Z to HIGH		2.6		2.9		3.3		3.9		5.5	ns
t _{ENZL}	Enable Pad Z to LOW		2.9		3.2		3.7		4.3		6.1	ns
t _{ENHZ}	Enable Pad HIGH to Z		4.9		5.4		6.2		7.3		10.2	ns
t _{ENLZ}	Enable Pad LOW to Z		5.3		5.9		6.7		7.9		11.1	ns
t _{GLH}	G-to-Pad HIGH		2.6		2.9		3.3		3.8		5.3	ns
t _{GHL}	G-to-Pad LOW		2.6		2.9		3.3		3.8		5.3	ns
t _{LSU}	I/O Latch Set-Up	0.5		0.5		0.6		0.7		1.0		ns
t _{LH}	I/O Latch Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{LCO}	I/O Latch Clock-to-Out (Pad-to-Pad), 64 Clock Loading		5.2		5.8		6.6		7.7		10.8	ns
t _{ACO}	Array Clock-to-Out (Pad-to-Pad), 64 Clock Loading		7.4		8.2		9.3		10.9		15.3	ns
d _{TLH}	Capacity Loading, LOW to HIGH		0.03		0.03		0.03		0.04		0.06	ns/pF
d _{THL}	Capacity Loading, HIGH to LOW		0.04		0.04		0.04		0.05		0.07	ns/pF

Table 38 •A42MX09 Timing Characteristics (Nominal 5.0 V Operation) (continued) (Worst-Case Commercial
Conditions, VCCA = 4.75 V, T_J = 70°C)

		–3 Sp	beed	–2 S	peed	–1 Sp	beed	Std S	Speed	–F S	peed	
Parame	ter / Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
CMOS C	Dutput Module Timing ⁵											
t _{DLH}	Data-to-Pad HIGH		2.4		2.7		3.1		3.6		5.1	ns
t _{DHL}	Data-to-Pad LOW		2.9		3.2		3.6		4.3		6.0	ns
t _{ENZH}	Enable Pad Z to HIGH		2.7		2.9		3.3		3.9		5.5	ns
t _{ENZL}	Enable Pad Z to LOW		2.9		3.2		3.7		4.3		6.1	ns
t _{ENHZ}	Enable Pad HIGH to Z		4.9		5.4		6.2		7.3		10.2	ns
t _{ENLZ}	Enable Pad LOW to Z		5.3		5.9		6.7		7.9		11.1	ns
t _{GLH}	G-to-Pad HIGH		4.2		4.6		5.2		6.1		8.6	ns
t _{GHL}	G-to-Pad LOW		4.2		4.6		5.2		6.1		8.6	ns
t _{LSU}	I/O Latch Set-Up	0.5		0.5		0.6		0.7		1.0		ns
t _{LH}	I/O Latch Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{LCO}	I/O Latch Clock-to-Out (Pad-to-Pad), 64 Clock Loading		5.2		5.8		6.6		7.7		10.8	ns
t _{ACO}	Array Clock-to-Out (Pad-to-Pad), 64 Clock Loading		7.4		8.2		9.3		10.9		15.3	ns
d _{TLH}	Capacity Loading, LOW to HIGH		0.03		0.03		0.03		0.04		0.06	ns/pF
d _{THL}	Capacity Loading, HIGH to LOW		0.04		0.04		0.04		0.05		0.07	ns/pF

Table 38 • A42MX09 Timing Characteristics (Nominal 5.0 V Operation) (continued)(Worst-Case Commercial Conditions, VCCA = 4.75 V, $T_J = 70^{\circ}$ C)

 For dual-module macros, use t_{PD1} + t_{RD1} + t_{PDn}, t_{CO} + t_{RD1} + t_{PDn}, or t_{PD1} + t_{RD1} + t_{SUD}, whichever is appropriate.
 Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual performance.

3. Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the Timer utility.

Set-up and hold timing parameters for the input buffer latch are defined with respect to the PAD and the D input. External 4. setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.

Delays based on 35 pF loading 5.

Table 39 •	A42MX09 Timing Characteristics (Nominal 3.3 V Operation) (Worst-Case Commercial Conditions,
	VCCA = 3.0 V, T _J = 70°C)

		-3 Speed -2 Speed -		-1 Speed	Std Speed	–F Speed	
Paramete	er / Description	Min. Max.	Min. Max.	Min. Max.	Min. Max.	Min. Max.	Units
Logic Mo	odule Propagation Delays ¹						
t _{PD1}	Single Module	1.6	1.8	2.1	2.5	3.5	ns
t _{CO}	Sequential Clock-to-Q	1.8	2.0	2.3	2.7	3.8	ns
t _{GO}	Latch G-to-Q	1.7	1.9	2.1	2.5	3.5	ns
t _{RS}	Flip-Flop (Latch) Reset-to-Q	2.0	2.2	2.5	2.9	4.1	ns
Logic Mo	odule Predicted Routing Delays ²						
t _{RD1}	FO = 1 Routing Delay	1.0	1.1	1.2	1.4	2.0	ns
t _{RD2}	FO = 2 Routing Delay	1.3	1.4	1.6	1.9	2.7	ns
t _{RD3}	FO = 3 Routing Delay	1.6	1.8	2.0	2.4	3.3	ns

			–3 S	peed	–2 Sp	beed	–1 Sj	beed	Std S	Speed	–F Sp	beed	
Paramete	er / Description		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
Logic Mo	odule Sequential Timi	ng ^{3, 4}											
t _{SUD}	Flip-Flop (Latch) Data Input Set-Up		0.5		0.5		0.6		0.7		0.9		ns
t _{HD}	Flip-Flop (Latch) Data	a Input Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{SUENA}	Flip-Flop (Latch) Ena	ble Set-Up	1.0		1.1		1.2		1.4		2.0		ns
t _{HENA}	Flip-Flop (Latch) Ena	ble Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse W	/idth	4.8		5.3		6.0		7.1		9.9		ns
t _{WASYN}	Flip-Flop (Latch) Asynchronous Pulse	Width	6.2		6.9		7.9		9.2		12.9		ns
t _A	Flip-Flop Clock Input	Period	9.5		10.6		12.0		14.1		19.8		ns
t _{INH}	Input Buffer Latch Ho	old	0.0		0.0		0.0		0.0		0.0		ns
t _{INSU}	Input Buffer Latch Se	et-Up	0.7		0.8		0.9		1.01		1.4		ns
t _{OUTH}	Output Buffer Latch H	lold	0.0		0.0		0.0		0.0		0.0		ns
t _{OUTSU}	Output Buffer Latch S	Set-Up	0.7		0.8		0.89		1.01		1.4		ns
f _{MAX}	Flip-Flop (Latch) Cloo Frequency	ck		129		117		108		94		56	MHz
Input Mo	dule Propagation Del	ays											
t _{INYH}	Pad-to-Y HIGH			1.5		1.6		1.9		2.2		3.1	ns
t _{INYL}	Pad-to-Y LOW			1.1		1.3		1.4		1.7		2.4	ns
t _{INGH}	G to Y HIGH			2.0		2.2		2.5		2.9		4.1	ns
t _{INGL}	G to Y LOW			2.0		2.2		2.5		2.9		4.1	ns
Input Mo	dule Predicted Routir	ng Delays ²											
t _{IRD1}	FO = 1 Routing Delay			2.6		2.9		3.2		3.8		5.3	ns
t _{IRD2}	FO = 2 Routing Delay			2.9		3.2		3.7		4.3		6.1	ns
t _{IRD3}	FO = 3 Routing Delay			3.3		3.6		4.1		4.9		6.8	ns
t _{IRD4}	FO = 4 Routing Delay			3.6		4.0		4.6		5.4		7.6	ns
t _{IRD8}	FO = 8 Routing Delay			5.1		5.6		6.4		7.5		10.5	ns
Global C	lock Network												
t _{СКН}	Input LOW to HIGH	FO = 32 FO = 384		4.4 4.8		4.8 5.3		5.5 6.0		6.5 7.1		9.0 9.9	ns ns
t _{CKL}	Input HIGH to LOW	FO = 32 FO = 384		5.3 6.2		5.9 6.9		6.7 7.9		7.8 9.2		11.0 12.9	ns ns
t _{PWH}	Minimum Pulse Width HIGH	FO = 32 FO = 384	5.7 6.6		6.3 7.4		7.1 8.3		8.4 9.8		11.8 13.7		ns ns

Table 41 • A42MX16 Timing Characteristics (Nominal 3.3 V Operation) (continued) (Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)

Table 41 • A42MX16 Timing Characteristics (Nominal 3.3 V Operation) (continued)(Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)

		–3 S	peed	–2 Sp	beed	–1 S	peed	Std S	Speed	–F S	peed	
Parame	eter / Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{ACO}	Array Clock-to-Out (Pad-to-Pad),64 Clock Loading		11.3		12.5		14.2		16.7		23.3	ns
d _{TLH}	Capacitive Loading, LOW to HIGH		0.04		0.04		0.05		0.06		0.08	ns/pF
d_{THL}	Capacitive Loading, HIGH to LOW		0.05		0.05		0.06		0.07		0.10	ns/pF

1. For dual-module macros use tPD1 + tRD1 + taped, to + tRD1 + taped, or tPD1 + tRD1 + tusk, whichever is appropriate.

2. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing ansalysis or simulation is required to determine actual performance.

3. Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the Timer utility.

4. Set-up and hold timing parameters for the input buffer latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G inputs subtracts (adds) to the internal setup (hold) time.

5. Delays based on 35 pF loading.

Table 42 •A42MX24 Timing Characteristics (Nominal 5.0 V Operation) (Worst-Case Commercial Conditions,
VCCA = 4.75 V, T_J = 70°C)

		–3 S	peed	–2 Sp	beed	–1 S	beed	Std S	peed	–F S	peed	
Parameter	/ Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
Logic Mod	dule Combinatorial Functions ¹											
t _{PD}	Internal Array Module Delay		1.2		1.3		1.5		1.8		2.5	ns
t _{PDD}	Internal Decode Module Delay		1.4		1.6		1.8		2.1		3.0	ns
Logic Mod	dule Predicted Routing Delays ²											
t _{RD1}	FO = 1 Routing Delay		0.8		0.9		1.0		1.2		1.7	ns
t _{RD2}	FO = 2 Routing Delay		1.0		1.2		1.3		1.5		2.1	ns
t _{RD3}	FO = 3 Routing Delay		1.3		1.4		1.6		1.9		2.6	ns
t _{RD4}	FO = 4 Routing Delay		1.5		1.7		1.9		2.2		3.1	ns
t _{RD5}	FO = 8 Routing Delay		2.4		2.7		3.0		3.6		5.0	ns
Logic Mod	dule Sequential Timing ^{3, 4}											
t _{CO}	Flip-Flop Clock-to-Output		1.3		1.4		1.6		1.9		2.7	ns
t _{GO}	Latch Gate-to-Output		1.2		1.3		1.5		1.8		2.5	ns
t _{SUD}	Flip-Flop (Latch) Set-Up Time	0.3		0.4		0.4		0.5		0.7		ns
t _{HD}	Flip-Flop (Latch) Hold Time	0.0		0.0		0.0		0.0		0.0		ns
t _{RO}	Flip-Flop (Latch) Reset-to-Output		1.4		1.6		1.8		2.1		2.9	ns
t _{SUENA}	Flip-Flop (Latch) Enable Set-Up	0.4		0.5		0.5		0.6		0.8		ns
t _{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	3.3		3.7		4.2		4.9		6.9		ns
t _{WASYN}	Flip-Flop (Latch) Asynchronous Pulse Width	4.4		4.8		5.3		6.5		9.0		ns

		–3 S	peed	–2 Sp	beed	–1 Sp	beed	Std S	peed	–F Sj	peed	
Parameter	/ Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
Input Mod	ule Propagation Delays											
t _{INPY}	Input Data Pad-to-Y		1.0		1.1		1.3		1.5		2.1	ns
t _{INGO}	Input Latch Gate-to-Output		1.3		1.4		1.6		1.9		2.6	ns
t _{INH}	Input Latch Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{INSU}	Input Latch Set-Up	0.5		0.5		0.6		0.7		1.0		ns
t _{ILA}	Latch Active Pulse Width	4.7		5.2		5.9		6.9		9.7		ns

Table 42 • A42MX24 Timing Characteristics (Nominal 5.0 V Operation) (continued) (Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)

		–3 S	peed	–2 S	peed	–1 Sp	beed	Std S	peed	–F Sp	beed	
Parame	ter / Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
TTL Out	tput Module Timing ⁵ (Continued)											
t _{ENLZ}	Enable Pad LOW to Z		4.9		5.5		6.2		7.3		10.2	ns
t _{GLH}	G-to-Pad HIGH		2.9		3.3		3.7		4.4		6.1	ns
t _{GHL}	G-to-Pad LOW		2.9		3.3		3.7		4.4		6.1	ns
t _{LSU}	I/O Latch Output Set-Up	0.5		0.5		0.6		0.7		1.0		ns
t _{LH}	I/O Latch Output Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{LCO}	I/O Latch Clock-to-Out (Pad-to-Pad) 32 I/O		5.7		6.3		7.1		8.4		11.8	ns
t _{ACO}	Array Latch Clock-to-Out (Pad-to-Pad) 32 I/O		7.8		8.6		9.8		11.5		16.1	ns
d _{TLH}	Capacitive Loading, LOW to HIGH		0.07		0.08		0.09		0.10		0.14	ns/pF
d _{THL}	Capacitive Loading, HIGH to LOW		0.07		0.08		0.09		0.10		0.14	ns/pF

Table 44 •A42MX36 Timing Characteristics (Nominal 5.0 V Operation)(Worst-Case Commercial Conditions,
VCCA = 4.75 V, T_J = 70°C)

Table 53 • PQ208

PQ208			
Pin Number	A42MX16 Function	A42MX24 Function	A42MX36 Function
95	NC	I/O	I/O
96	NC	I/O	I/O
97	NC	I/O	I/O
98	VCCI	VCCI	VCCI
99	I/O	I/O	I/O
100	I/O	WD, I/O	WD, I/O
101	I/O	WD, I/O	WD, I/O
102	I/O	I/O	I/O
103	SDO, I/O	SDO, TDO, I/O	SDO, TDO, I/O
104	I/O	I/O	I/O
105	GND	GND	GND
106	NC	VCCA	VCCA
107	I/O	I/O	I/O
108	I/O	I/O	I/O
109	I/O	I/O	I/O
110	I/O	I/O	I/O
111	I/O	I/O	I/O
112	NC	I/O	I/O
113	NC	I/O	I/O
114	NC	I/O	I/O
115	NC	I/O	I/O
116	I/O	I/O	I/O
117	I/O	I/O	I/O
118	I/O	I/O	I/O
119	I/O	I/O	I/O
120	I/O	I/O	I/O
121	I/O	I/O	I/O
122	I/O	I/O	I/O
123	I/O	I/O	I/O
124	I/O	I/O	I/O
125	I/O	I/O	I/O
126	GND	GND	GND
127	I/O	I/O	I/O
128	I/O	TCK, I/O	TCK, I/O
129	LP	LP	LP
130	VCCA	VCCA	VCCA
131	GND	GND	GND

Table 54 • PQ24	40
PQ240	
Pin Number	A42MX36 Function
163	WD, I/O
164	WD, I/O
165	I/O
166	QCLKA, I/O
167	I/O
168	I/O
169	I/O
170	I/O
171	I/O
172	VCCI
173	I/O
174	WD, I/O
175	WD, I/O
176	I/O
177	I/O
178	TDI, I/O
179	TMS, I/O
180	GND
181	VCCA
182	GND
183	I/O
184	I/O
185	I/O
186	I/O
187	I/O
188	I/O
189	I/O
190	I/O
191	I/O
192	VCCI
193	I/O
194	I/O
195	I/O
196	I/O
197	I/O
198	I/O
199	I/O

VQ80		
Pin Number	A40MX02 Function	A40MX04 Function
49	I/O	I/O
50	CLK, I/O	CLK, I/O
51	I/O	I/O
52	MODE	MODE
53	VCC	VCC
54	NC	I/O
55	NC	I/O
56	NC	I/O
57	SDI, I/O	SDI, I/O
58	DCLK, I/O	DCLK, I/C
59	PRA, I/O	PRA, I/O
60	NC	NC
61	PRB, I/O	PRB, I/O
62	I/O	I/O
63	I/O	I/O
64	I/O	I/O
65	I/O	I/O
66	I/O	I/O
67	I/O	I/O
68	GND	GND
69	I/O	I/O
70	I/O	I/O
71	I/O	I/O
72	I/O	I/O
73	I/O	I/O
74	VCC	VCC
75	I/O	I/O
76	I/O	I/O
77	I/O	I/O
78	I/O	I/O
79	I/O	I/O
30	I/O	I/O

Figure 50 • CQ256



A42MX36 Function
NC
GND
I/O
GND
I/O

PG132	
Pin Number	A42MX09 Function
B3	I/O
A2	I/O
C3	DCLK
B5	GNDA
E12	GNDA
J2	GNDA
M9	GNDA
В9	GNDI
C5	GNDI
E11	GNDI
F4	GNDI
J3	GNDI
J11	GNDI
L5	GNDI
L9	GNDI
C9	GNDQ
E3	GNDQ
K12	GNDQ
D7	VCCA
G3	VCCA
G10	VCCA
L7	VCCA
C7	VCCI
G2	VCCI
G11	VCCI
K7	VCCI

Table 62 •	CQ172
21	I/O
22	GND
23	VCCI
24	VSV
25	I/O
26	I/O
27	VCC
28	I/O
29	I/O
30	I/O
31	I/O
32	GND
33	I/O
34	I/O
35	I/O
36	I/O
37	GND
38	I/O
39	I/O
40	I/O
41	I/O
42	I/O
43	I/O
44	BININ
45	BINOUT
46	I/O
47	I/O
48	I/O
49	I/O
50	VCCI
51	I/O
52	I/O
53	I/O
54	I/O
55	GND
56	I/O
57	I/O
58	I/O
59	I/O